Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C

Supporting Information

Improved performance in TIPS-pentacene field effect transistors using solvent additives

Gil Jo Chae,[†] Seung-Hyeon Jeong,[‡] Jeong Hoon Baek,[†] Bright Walker,[§] Chung Kun Song,[‡,*] Jung Hwa Seo,[†,*]

[†]Department of Materials Physics, Dong-A University, Busan 604-714, South Korea

[‡]Department of Electronics Engineering, Dong-A University, Busan 604-714, South Korea

[§]Department of Interdisciplinary Green Energy, Ulsan National Institute of Science and Technology, Ulsan 689-798, South Korea

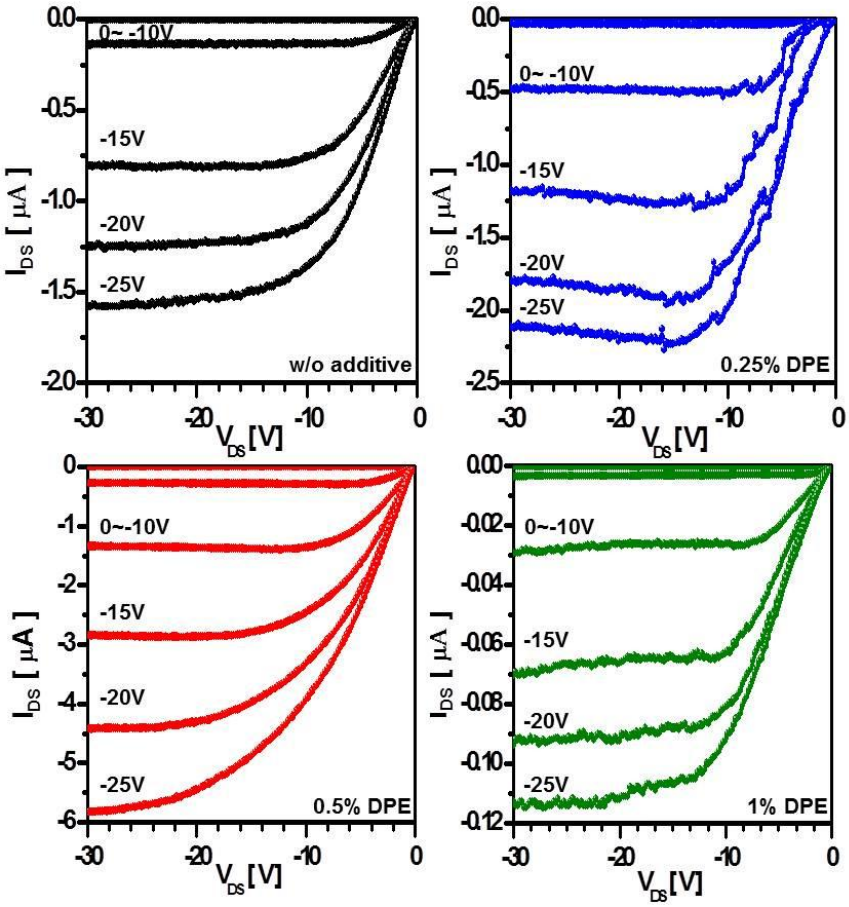


Figure S1. Output characteristics of TIPS-pentacene FETs processed using various DPE concentrations.

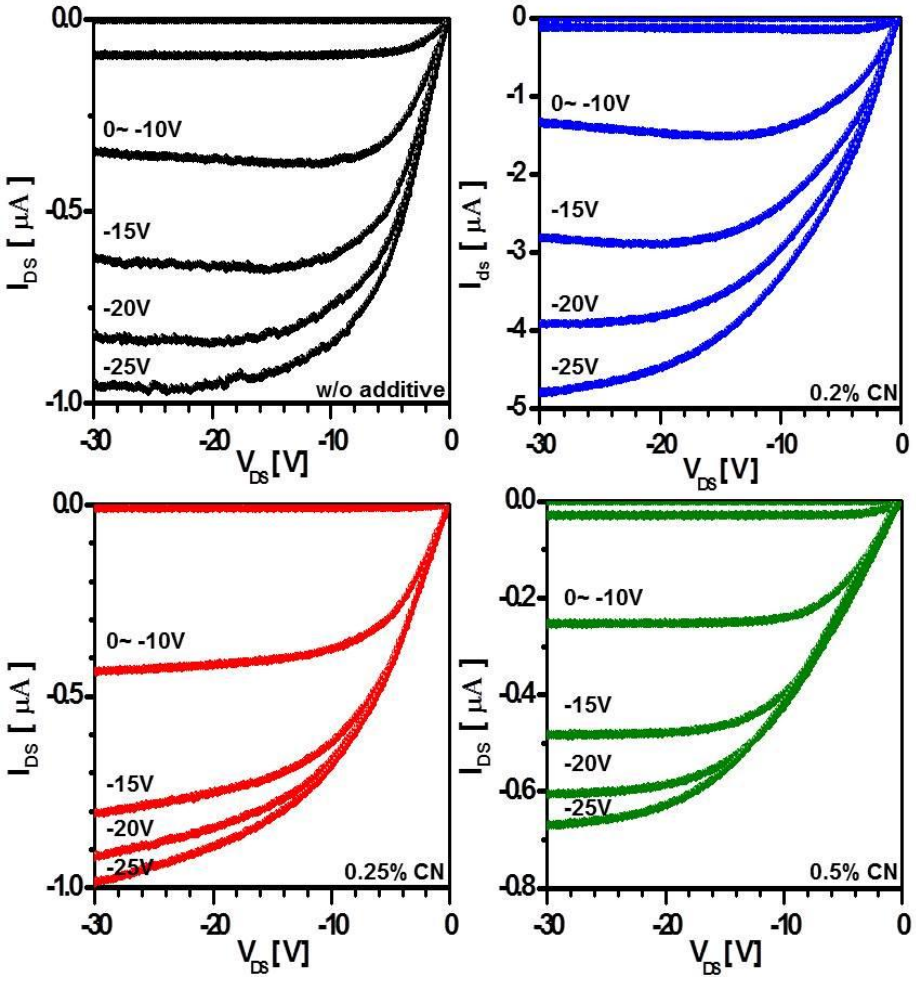


Figure S2. Output characteristics of TIPS-pentacene FETs processed using various CN concentrations.

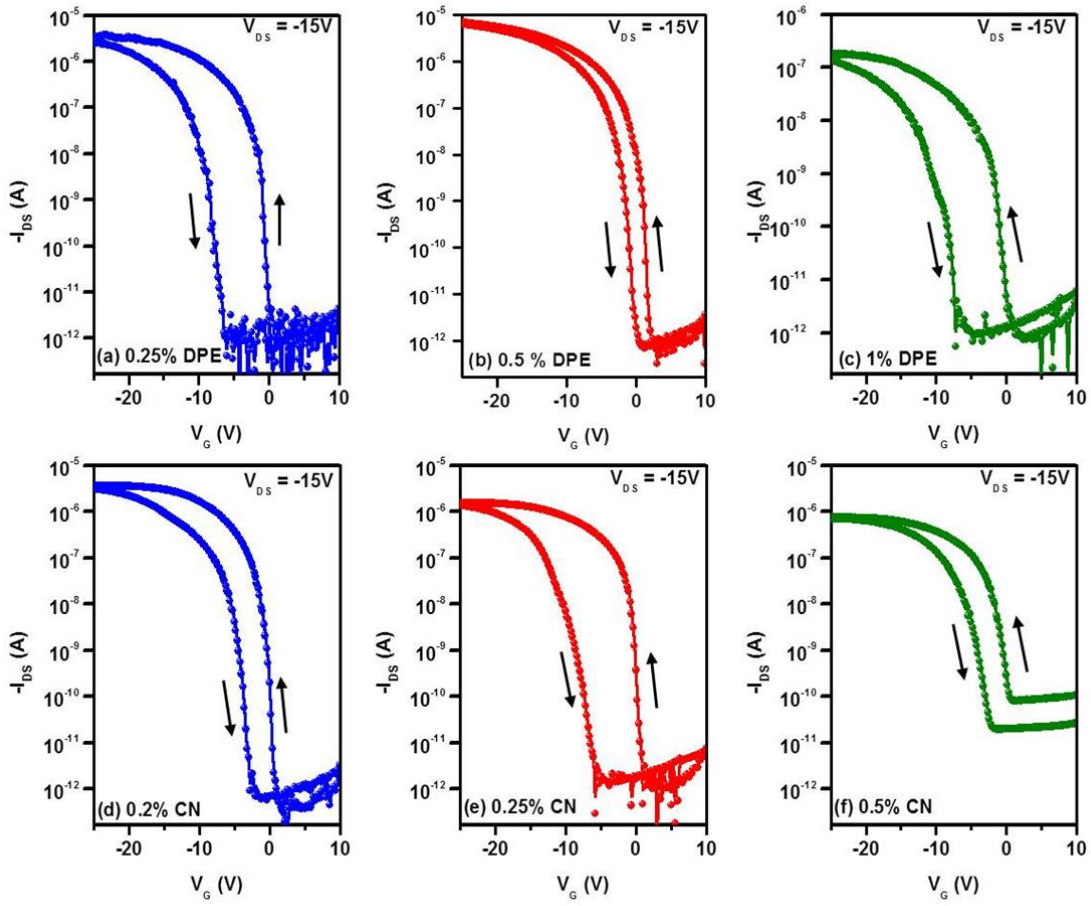
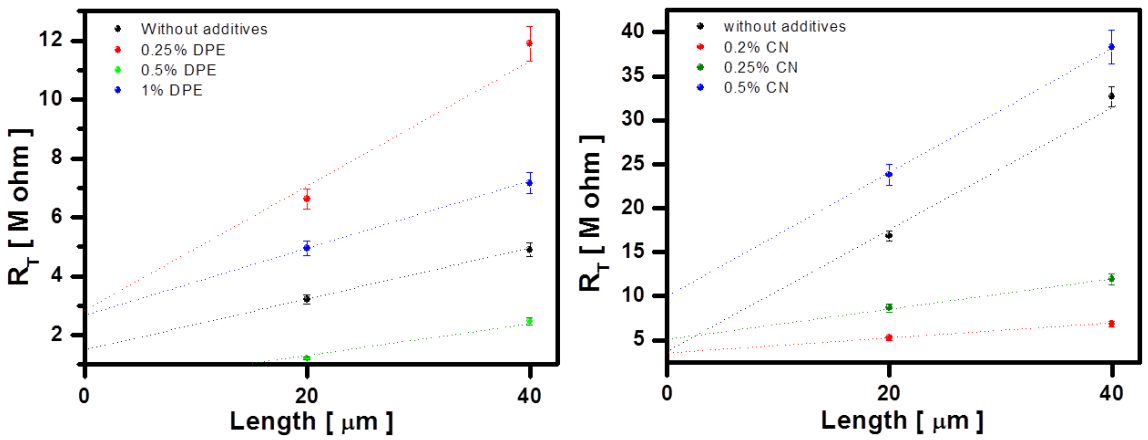


Figure S3. Transfer hysteresis characteristics of TIPS-pentacene FETs with various concentration of DPE and CN.



(a) (b)

Figure S4. Total resistance (R_T) *vs.* channel length of TIPS-pentacene FETs with (a) DPE and (b) CN at different additive concentrations.

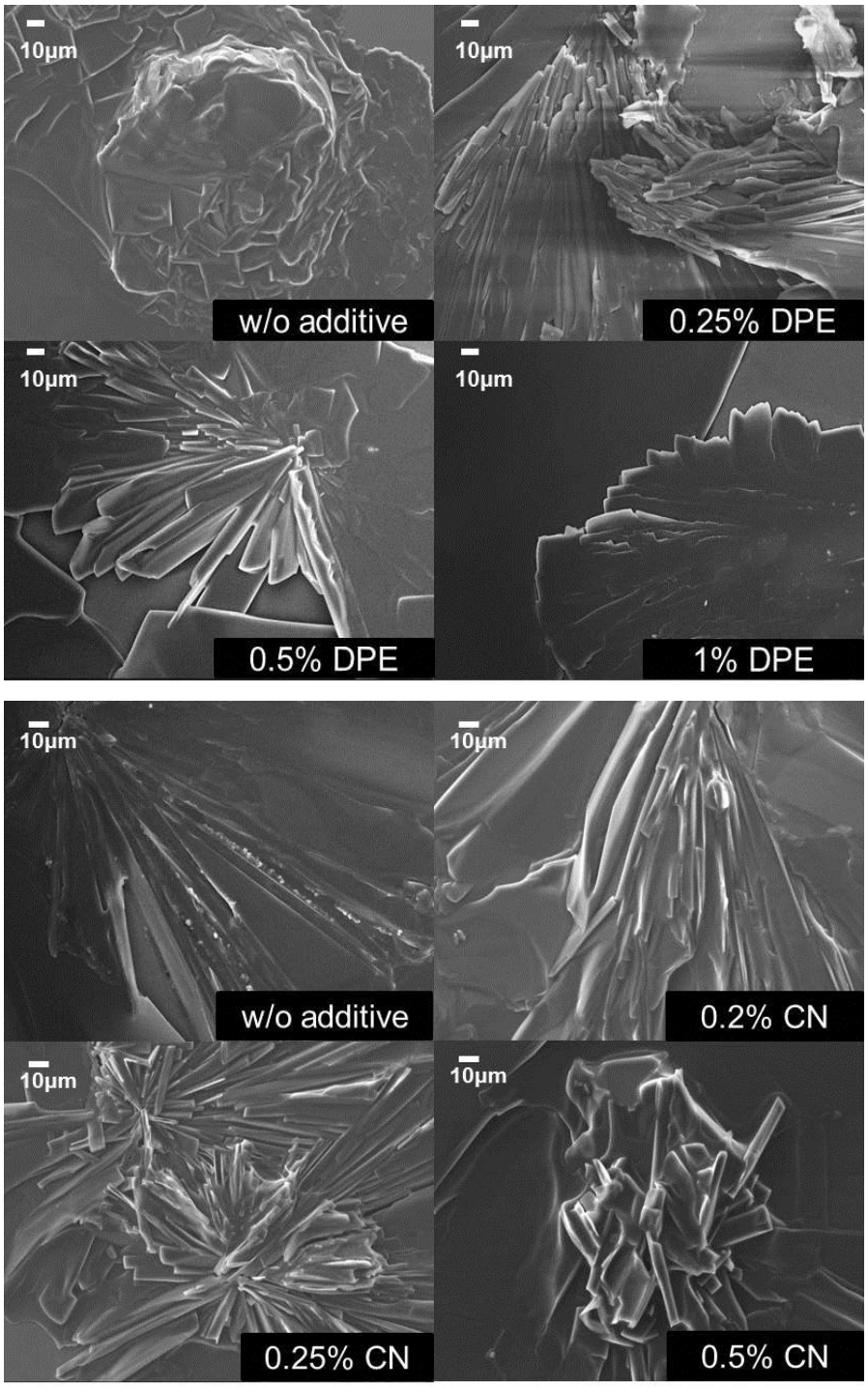


Figure S5. SEM images (× 500) of TIPS-pentacene films processed with various DPE (top) and CN (bottom) concentrations.

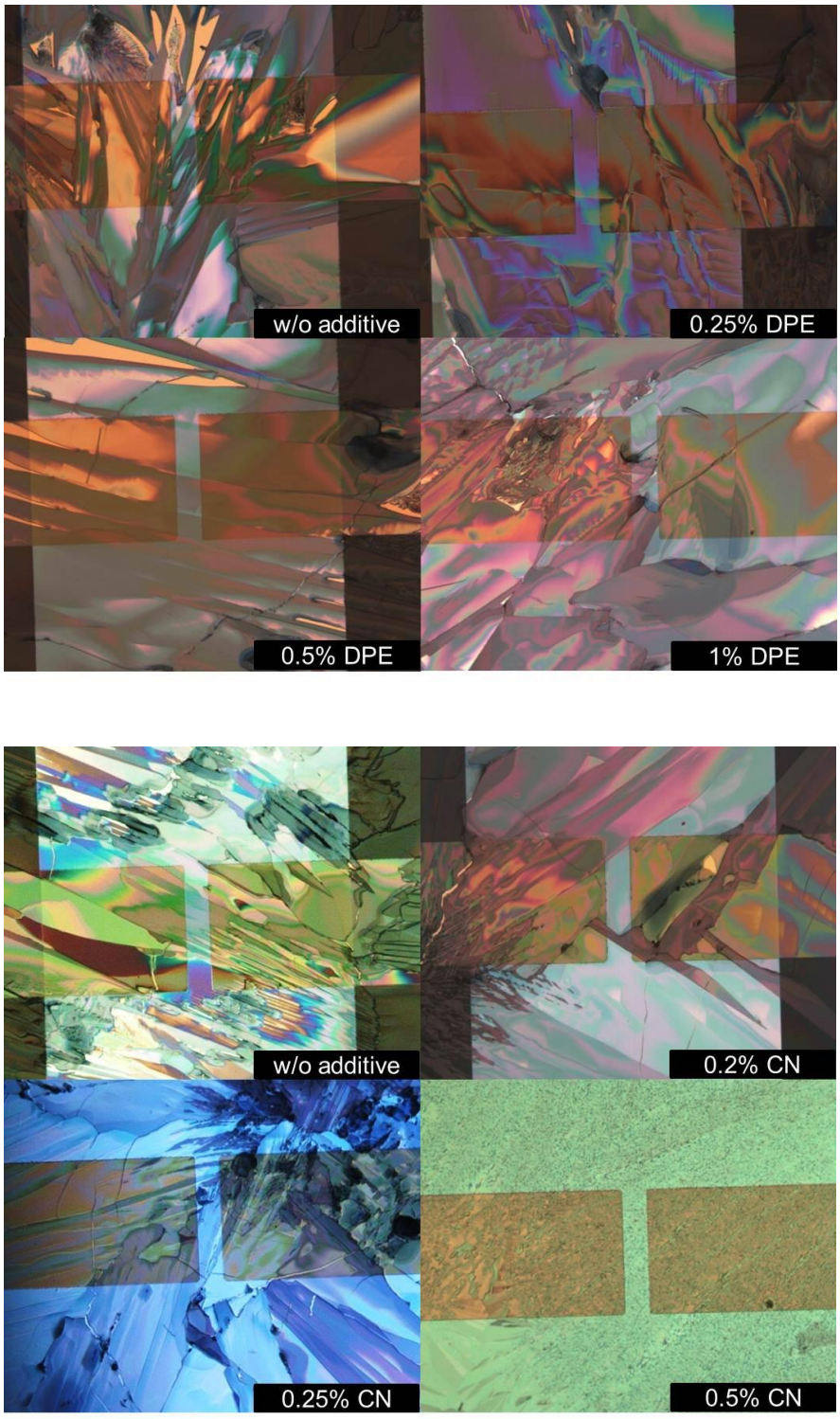


Figure S6. Optical microscope images of TIPS-pentacene FETs processed with various DPE (top) and CN (bottom) concentrations.

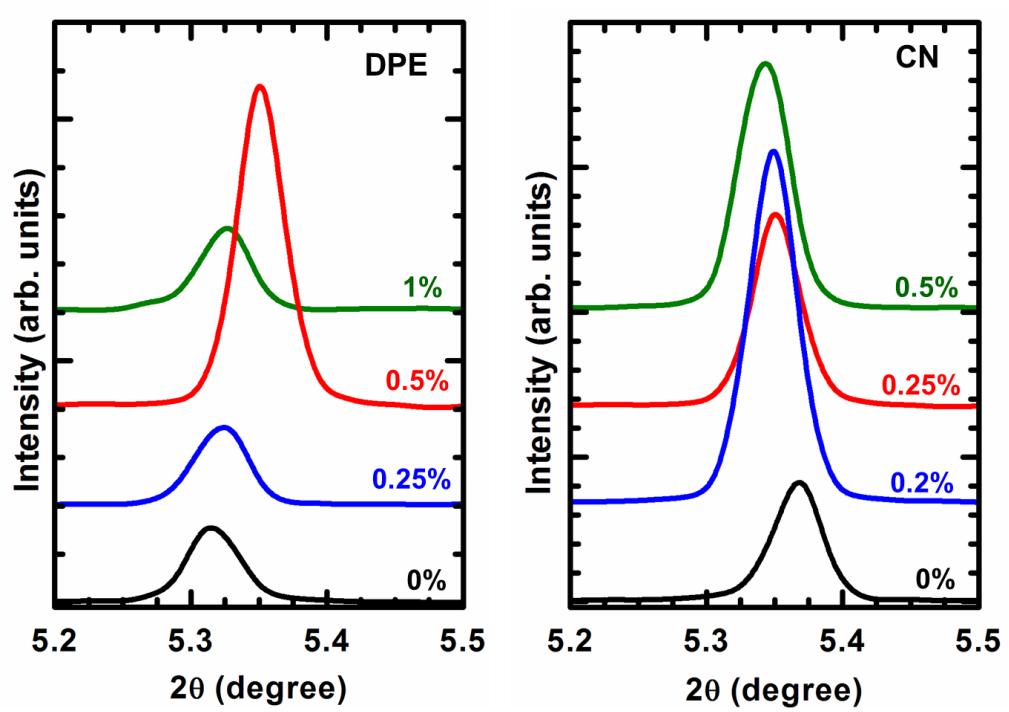


Figure S7. XRD (001) peaks for TIPS-pentacene films processed with various concentrations of DPE (left) and CN (right).

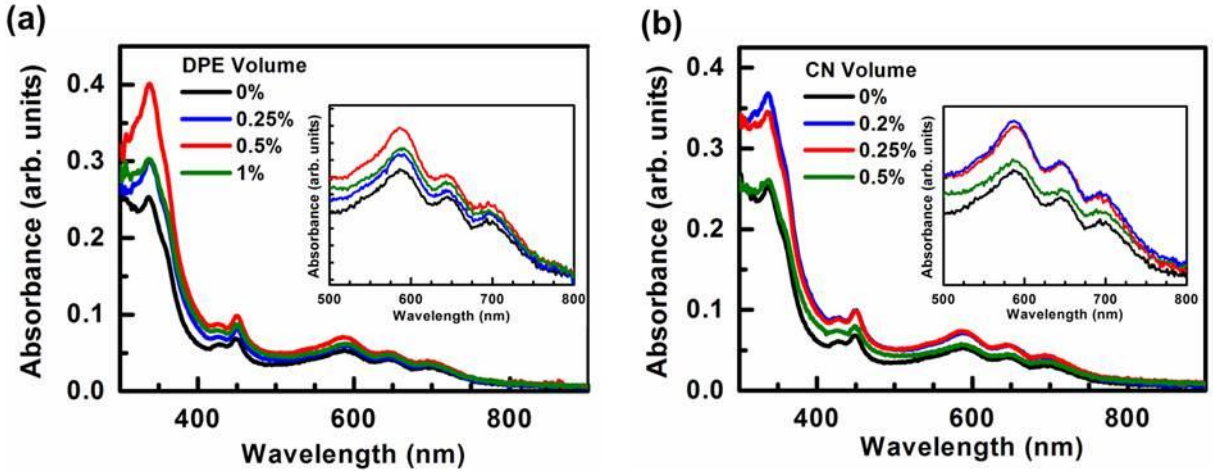


Figure S8. UV-Vis absorption spectra of TIPS-pentacene films processed with (a) DPE and (b) CN prepared using different additive concentrations.